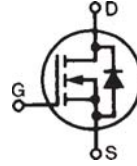


HiPerFET™ Power MOSFET Q2-Class

IXFL38N100Q2

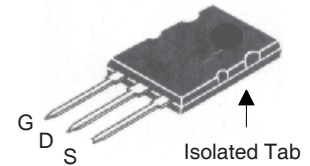
N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , Low Intrinsic R_G
High dV/dt , Low t_{rr}



$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 29A \\ R_{DS(on)} &\leq 280m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 1000 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$ | 1000 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 29 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 152 | A |
| I_A | $T_C = 25^\circ\text{C}$ | 38 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 5 | J |
| dV/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$ | 20 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 380 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.063 in.) from case for 10s | 300 | $^\circ\text{C}$ |
| T_{sOLD} | Plastic body for 10s | 260 | $^\circ\text{C}$ |
| F_C | Mounting force | 30..120/6.7..27 | N/lbs |
| V_{ISOL} | 50/60 Hz, RMS $t = 1$ min | 2500 | V~ |
| | $I_{ISOL} \leq 1$ mA $t = 1$ s | 3000 | V~ |
| Weight | | 10 | g |

ISOPLUS264™ (IXFL)



G = Gate D = Drain
S = Source

Features

- Electrically isolated mounting tab
- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic diode

Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies
- DC choppers
- Pulse generation
- Laser drivers

Advantages

- 2500 V~ Electrical isolation
- ISOPLUS 264™ package for clip or spring mounting
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---------------------------------------|---|------|--|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0$ V, $I_D = 1$ mA | 1000 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8$ mA | 3.0 | | V |
| I_{GSS} | $V_{GS} = \pm 30$ V, $V_{DS} = 0$ V | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ $V_{GS} = 0$ V | | | 100 μ A 5 mA $T_J = 125^\circ\text{C}$ |
| $R_{DS(on)}$ | $V_{GS} = 10$ V, $I_D = 19$ A, Note 1 | | | 280 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}, I_D = 19\text{A}$, Note 1 | 24 | 40 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 13.5 | nF |
| C_{oss} | | | 1035 | pF |
| C_{rss} | | | 180 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 19\text{A}$ $R_G = 1\Omega$ (External) | | 25 | ns |
| t_r | | | 28 | ns |
| $t_{d(off)}$ | | | 57 | ns |
| t_f | | | 15 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 19\text{A}$ | | 250 | nC |
| Q_{gs} | | | 60 | nC |
| Q_{gd} | | | 105 | nC |
| R_{thJC} | | | 0.33 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.13 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 38 A |
| I_{SM} | Repetitive, pulse width limited by T_{JM} | | | 152 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 25\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ | | | 300 ns |
| Q_{RM} | | | 1.4 | μC |
| I_{RM} | | | 9.0 | A |

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ISOPLUS264™ (IXFL) Outline

Note: Bottom heatsink meets

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| A2 | .046 | .055 | 1.17 | 1.40 |
| b | .045 | .055 | 1.14 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .111 | .126 | 2.82 | 3.20 |
| c | .020 | .029 | 0.51 | 0.74 |
| D | 1.020 | 1.040 | 25.91 | 26.42 |
| E | .770 | .788 | 19.56 | 20.09 |
| e | .215 BSC | | 5.46 BSC | |
| L | .780 | .820 | 19.81 | 20.83 |
| L1 | .080 | .102 | 2.03 | 2.59 |
| Q | .210 | .235 | 5.33 | 5.97 |
| Q1 | .490 | .513 | 12.45 | 13.03 |
| R | .150 | .180 | 3.81 | 4.57 |
| R1 | .100 | .130 | 2.54 | 3.30 |
| S | .668 | .690 | 16.97 | 17.53 |
| T | .801 | .821 | 20.34 | 20.85 |
| U | .065 | .080 | 1.65 | 2.03 |

Ref: IXYS CO 0128

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

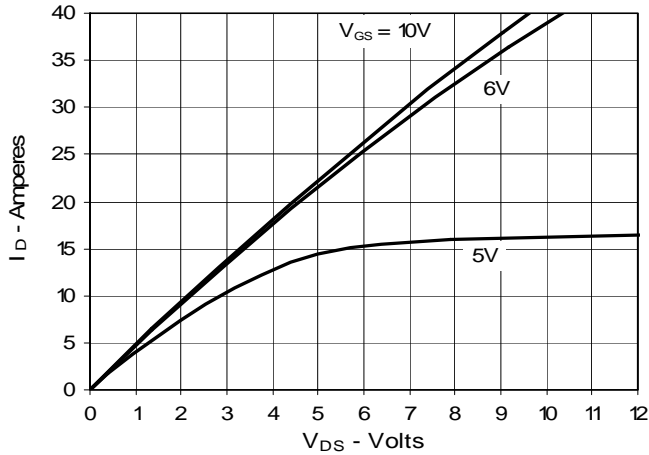


Fig. 2. Extended Output Characteristics @ 25°C

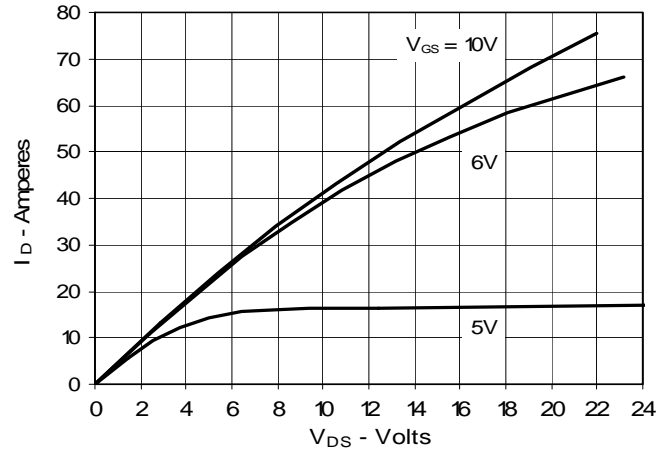


Fig. 3. Output Characteristics @ 125°C

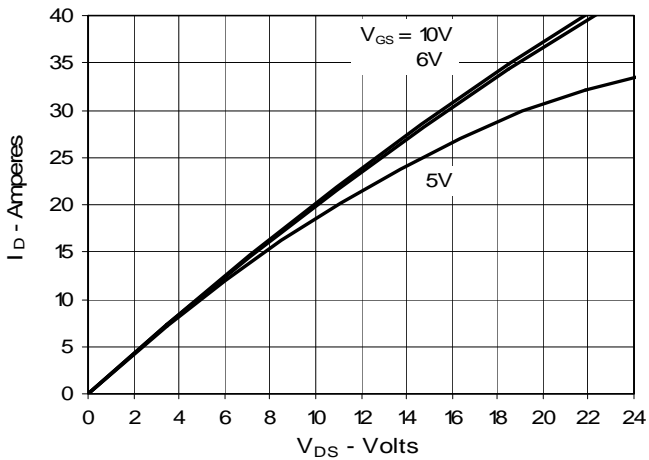


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 19A$ Value vs. Junction Temperature

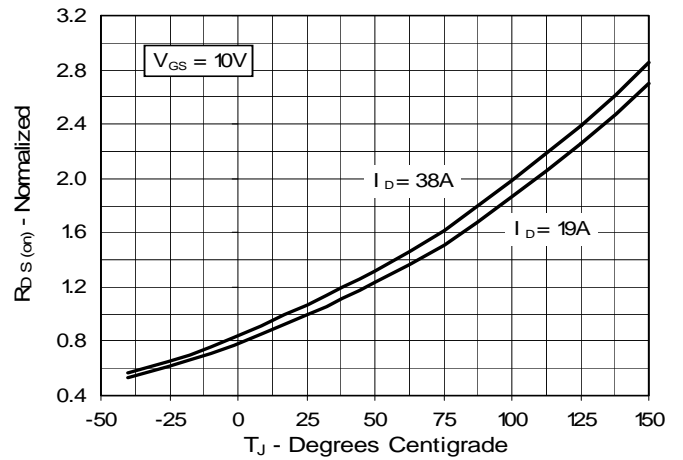


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 19A$ Value vs. Drain Current

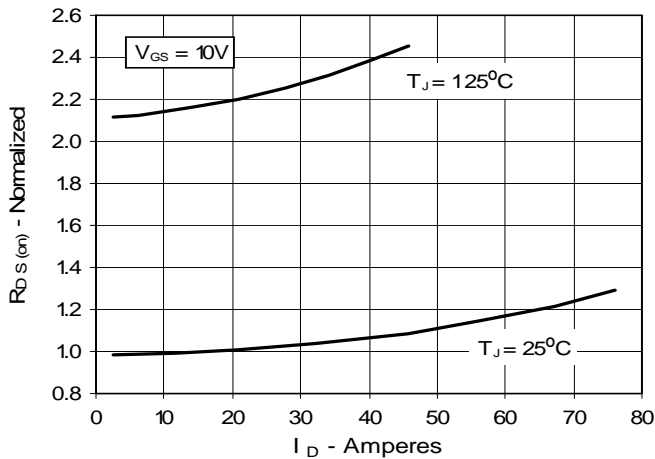


Fig. 6. Drain Current vs. Case Temperature

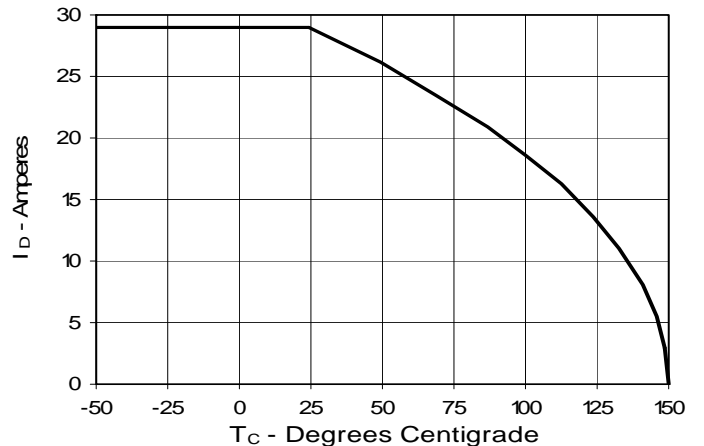


Fig. 7. Input Admittance

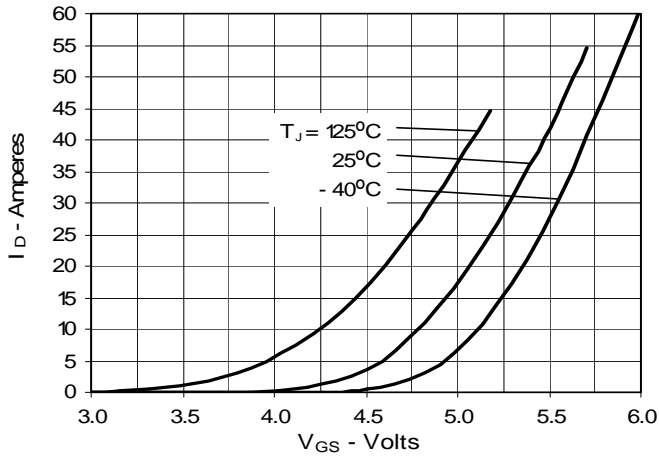


Fig. 8. Transconductance

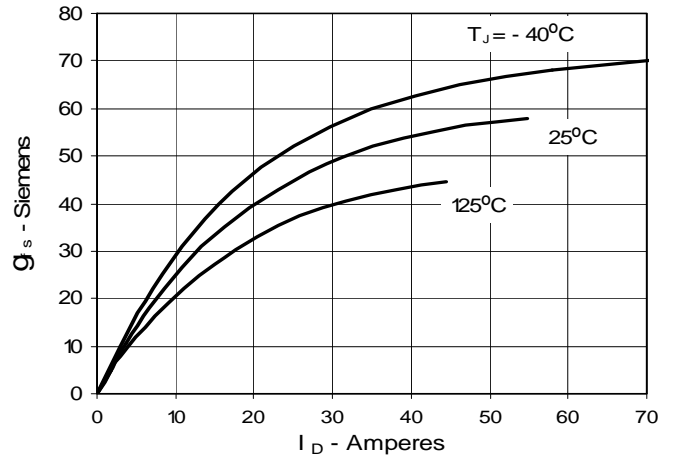


Fig. 9. Source Current vs. Source-To-Drain Voltage

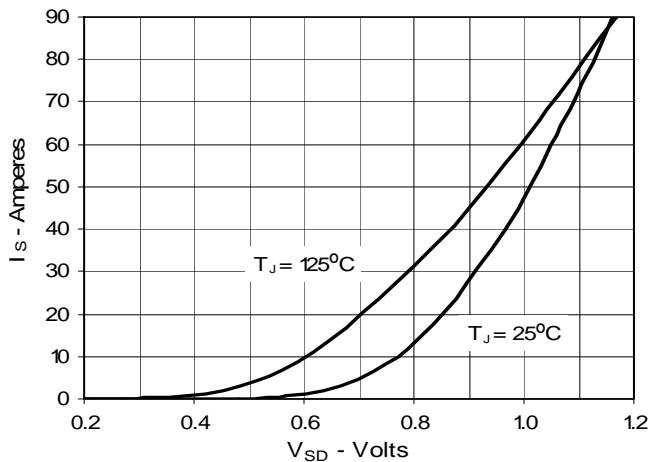


Fig. 10. Gate Charge

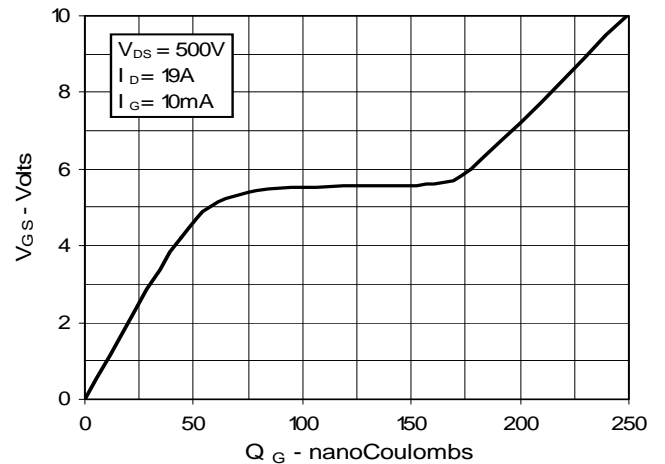


Fig. 11. Capacitance

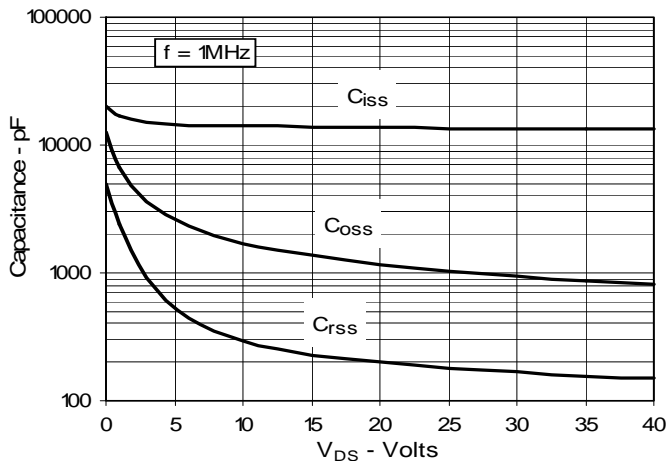


Fig. 12. Maximum Transient Thermal Impedance

